

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
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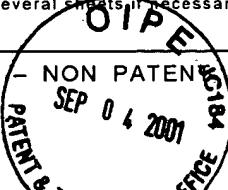
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Kie Y. Ahn et al..

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Examiner Cite

Initials No.¹

TL		YING SHI ET AL., "Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics," 3 pages (1998).
TL		W.-H. LEE ET AL., "A Novel High-k Inter-Poly Dielectric (IPD), Al ₂ O ₃ for Low Voltage/High speed Flash Memories: Erasing in msec at 3.3V," p. 117-118, (1997).
TL		XIN GUO ET AL., "High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS technology," 4 pages, (1999).
TL		H.F. LUAN ET AL., "High quality Ta ₂ O ₅ gate dielectrics with T _{ox,eq} <10 Å," 4 pages, (1999).
TL	v	K.J. HUBBARD ^{a)} ET AL., "Thermodynamic stability of binary oxides in contact with silicon," p. 2757-2776, (1996).
TL	v	B. CHENG ET AL., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's," p. 1537-1544, (1999).
TL	q	C.T. LIU, "Circuit Requirement and Integration Challenges of Thin Gate Dielectrics for Ultra Small MOSFETs," 4 pages, (1998).
TL	s	B.H. LEE ET AL., "Ultrathin Hafnium Oxide with Low Leakage and Excellent Reliability for Alternative Gate Dielectric Application," 4 pages, (1999).
TL	s	S.P. MURARKA ET AL., "Thermal oxidation of hafnium silicide films on silicon," 3 pages, (1980).
TL	q	ALBERT CHIN ET AL., "High Quality La ₂ O ₃ and Al ₂ O ₃ Gate Dielectric with Equivalent Oxide Thickness 5-10Å," 2 pages, (2000).
TL	v	D.A. MULLER ET AL., "The electronic structure at the atomic scale of ultrathin gate oxides," 4 pages, (1999).
TL		Y. SAITO ET AL, "High-Integrity Silicon Oxide Grown at Low-Temperature by Atomic Oxygen Generated in High-Density Krypton Plasma," 2 pages, (1999).

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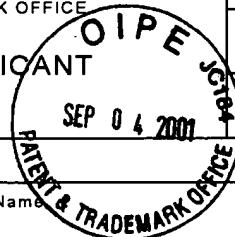
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U.S. PATENT DOCUMENTS

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